

REMARKS

Claims 1-50 are pending in the application with claim 43 amended herein. No amendment was made related the statutory requirements of patentability unless expressly stated herein. The amendments made herein now more positively express limitations that were previously inherent in such claim, and accordingly, are not for the purpose of narrowing and do not effectively narrow the scope of any claim. The title is amended herein in keeping with the suggestion of the Office Action. The amendment to claim 43 remedies the alleged informalities objected to in the Office Action. Applicants request withdrawal of the claim 43 objection.

Claims 1-35 stand rejected as being unpatentable over Huang in view of Gonzalez. Applicants request reconsideration. Applicants note that Gonzalez qualifies as prior art only under one or more of subsections (e), (f), and (g) of 35 U.S.C. 102. The subject matter of Gonzalez and of claims 1-35 were, at the time the invention was made, owned by Micron Technology, Inc. or subject to an obligation of assignment to Micron Technology, Inc. as evidenced by recorded assignments pertaining to in the present application and to Gonzalez. According to 35 U.S.C. 103(c), Gonzalez cannot preclude patentability under section 103. Thus, Applicants request withdrawal of the rejection and allowance of claims 1-35 in the next Office Action.

Claims 36-50 stand rejected as being unpatentable over Prall in view of Gonzalez. Applicants request reconsideration. As indicated above, Gonzalez cannot preclude patentability under section 103 for the reasons discussed above. Accordingly, Applicants request withdrawal of the rejection and allowance of claims 36-50 in the next Office Action.

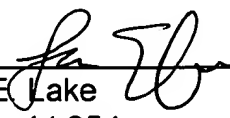
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At least for the reasons discussed above, claims 1-50 are patentable over all cited references considered alone or in combination. Applicants request allowance of all pending claims in the next Office Action.

Respectfully submitted,

Dated: 01 Jul 2002

By: _____


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Application Serial No. 09/879,335
Filing Date June 11, 2001
Inventor Vishnu K. Agarwal, et al
Assignee Micron Technology, Inc.
Group Art Unit 2813
Examiner Y. Huynh
Attorney's Docket No. MI22-1568
Title: Capacitor Forming Methods

**VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING
RESPONSE TO DECEMBER 11, 2001 OFFICE ACTION**

In the Specification

The replacement specification paragraphs incorporate the following amendments.

Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

The title has been amended as follows:

Capacitor Forming Methods ~~and Capacitor Constructions~~

The paragraph beginning at line 4 on page 1 has been amended as follows:

--This patent resulted from a continuation-in-part application of U.S. Patent Application Serial No. 09/710,546, filed on November 8, 2000 entitled "Semiconductor Processing Method" and naming Kunal R. Parekh and Randhir P.S. Thakur as inventors, which application is a continuation application of U.S. Patent No. 6,165,833, issued on ~~December 26, 2000~~ filed on December 19, 1997, each of which are herein incorporated by reference.--

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In the Claims

The claims have been amended as follows. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

43. (amended) A capacitor forming method comprising:

forming an insulation layer over a substrate, the substrate including an electronic device;

forming an opening into the insulation layer, the opening having a sidewall;

forming a capacitor electrode at least within the opening and over the sidewall;

forming a high K capacitor dielectric layer at least over the capacitor electrode;

after forming the high K capacitor dielectric layer, forming a barrier layer to V_t

shift inducing material at least over the insulation layer; and

providing V_t shift inducing material over the barrier layer, the barrier layer

retarding movement of the V_t shift inducing material into the electronic device.

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